Claim Amendments:

1. (cancelled)

2. (cancelled)

3. (cancelled)

4. (cancelled)

5. (cancelled)

6. (cancelled)

7. (cancelled)

8. (cancelled)

9. (cancelled)

10. (cancelled)

11. (cancelled)

12. (cancelled)

13. (cancelled)

14. (original): A method of fabrication of a slider for reading data from a disk surface, said slider having a magneto-resistive transducer including a stack of layers, and electrical leads attached to said transducer, said electrical leads having a proximal end which is proximal to said disk surface, comprising the steps of:

A) forming a first ferromagnetic layer having an end which will be proximal to said disk surface;

B) forming a non-magnetic metal layer on said first ferromagnetic layer, said non-magnetic metal layer having an end which will be proximal to said disk surface;

C) forming a second ferromagnetic layer on said non-magnetic metal layer, second ferromagnetic layer having an end which will be proximal to said disk surface;

D) forming an antiferromagnetic layer on said second ferromagnetic layer, said antiferromagnetic layer having an end which will be proximal to said disk surface;

E) recessing at least one of said proximal ends of said non-magnetic metal layer and said electrical leads from said disk surface to form at least one recessed area; and

F) filling said at least one recessed area with protective material.

15. (original) The method of fabrication as recited in claim 14, further comprising:

G) applying a layer of protective material to said proximal ends of the stacked layers and said electrical leads.

16. (original) The method of fabrication as recited in claim 14, wherein:

said recessing step E is performed by an operation chosen from the group consisting of wet etching, dry etching, reactive ion etching, and reactive ion beam etching.

17. (original) The method of fabrication as recited in claim 14, wherein:

said filling step F is performed by an operation chosen from the group consisting of ion beam deposit (IBD), chemical vapor deposition (CVD), physical vapor deposition (PVD) and sputtering deposition.

18. (original) The method of fabrication as recited in claim 14, wherein:

said at least one of said proximal ends which is recessed from said disk surface is said non-magnetic metal layer.

19. (original) The method of fabrication as recited in claim 14, wherein:

said at least one of said proximal ends which is recessed from said disk surface is at least one of said plurality of electrical leads.

20. (original) The method of fabrication as recited in claim 14, wherein:

said protective material which is used to fill said recessed area is chosen from a group consisting of Diamond-Like Carbon, silicon and silicon nitride.

21. (original) The method of fabrication as recited in claim 15, wherein:

said layer of protective material and said protective material which is used to fill said recessed area is the same, and filling step F and said applying step G are performed in the same process.

22. (cancelled)